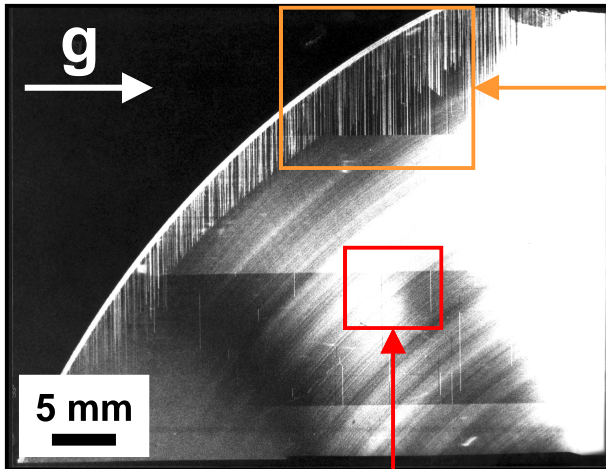
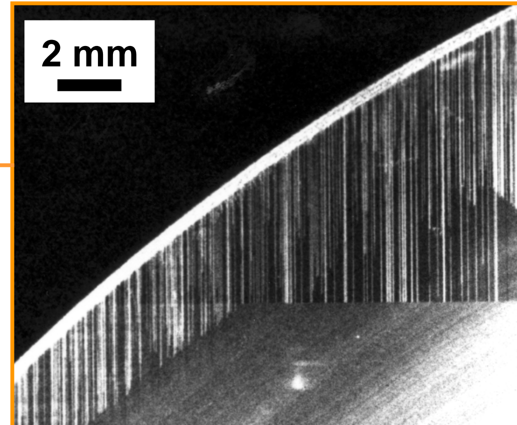
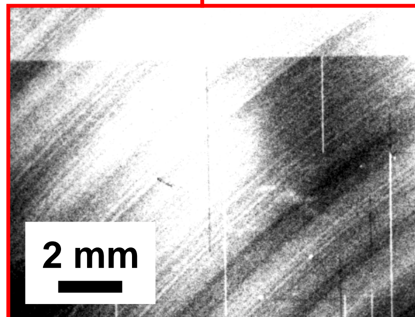
Double Crystal X-Ray Topography: Dose 10^{14} cm^2, After Annealing

(224) Reflection





The pre-existing misfit dislocations elongated within the non-implanted region and did not extend into the implanted region.



New misfit dislocations nucleated only in the non-implanted region.

P/p+ Si sample covered with stripes of photoresist and Si self-implanted, dose 10^{14} cm^2. Annealing at 900 °C for 25 minutes.

P. Feichtinger, H. Fukuto, R. Sandhu, B. Poust, and M. S. Goorsky, in *Ion implantation and misfit dislocation formation in p/p+ silicon*, Boston, MA, 1999 (Materials Research Society).